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Yue Lin,1,2 Yong Zhang,1,a) Zhiqiang Liu,3 Liqin Su,1 Jihong Zhang,2 Tongbo Wei,3 and Zhong Chen2

1Electrical and Computer Engineering Department, University of North Carolina at Charlotte, Charlotte, North Carolina 28223, USA
2Department of Electronic Science and Fujian Engineering Research Center for Solid-State Lighting, Xiamen University, Xiamen, Fujian 361005, People’s Republic of China
3R&D Center for Semiconductor Lighting, Chinese Academy of Sciences, Beijing 100083, People’s Republic of China

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The two legends in Figure 1, “type I” and “type II,” are reversed in the originally published version.1 The corrected version is showed in Fig. 1 herein.

FIG. 1. Two distinctly different types of droop behaviors observed in InGaN QW LEDs.


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Figure 1: Two distinctly different types of droop behaviors observed in InGaN QW LEDs.

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Yong Zhang, yong.zhang@uncc.edu